

COMPLEMENTARY SILICON POWER DARLINGTON TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- COMPLEMENTARY PNP NPN DEVICES
- MONOLITHIC DARLINGTON CONFIGURATION
- INTEGRATED ANTIPARALLEL COLLECTOR-EMITTER DIODE

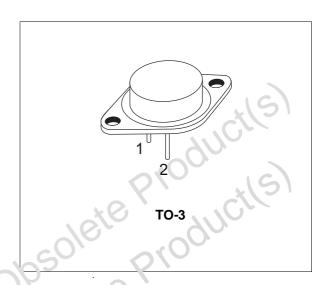
APPLICATIONS

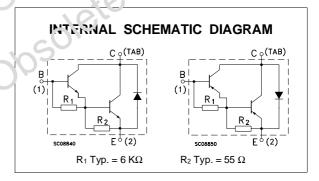
- GENERAL PURPOSE SWITCHING
- GENERAL PURPOSE AMPLIFIERS

DESCRIPTION

The MJ4035 is a silicon Epitaxial-Base NPN power transistor in monolithic Darlington configuration mounted in Jedec TO-3 metal case. It is inteded for use in general purpose and amplifier applications.

The complementary PNP type is the MJ4032





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
GO.		PNP	MJ4032	
103		NPN	MJ4035	
V_{CBO}	Collector-Base Voltage (I _E = 0)	100	V	
V_{CEO}	Collector-Emitter Voltage (I _B = 0)	100	V	
V_{EBO}	Emitter-Base Voltage (I _C = 0)	5	V	
Ic	Collector Current	16	Α	
lΒ	Base Current	0.5	Α	
P _{tot}	Total Dissipation at T _c ≤ 25 °C	150	W	
T _{stg}	Storage Temperature	-65 to 200	°C	
T_j	Max. Operating Junction Temperature	200	°C	

For PNP types voltage and current values are negative.

September 2003

THERMAL DATA

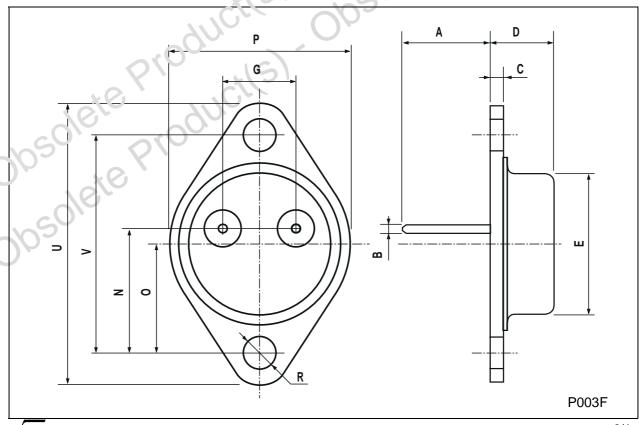
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Collector Cut-off Current ($R_{BE} = 1K\Omega$) Collector Cut-off Current ($I_B = 0$) Emitter Cut-off Current $I_C = 0$) Collector-Emitter Breakdown Voltage Collector-Emitter Saturation Voltage Collector-Emitter Co	$V_{CE} = 100 \text{ V}$ $V_{CE} = 100 \text{ V}$ $V_{CE} = 50 \text{ V}$ $V_{EB} = 5 \text{ V}$ $I_{C} = 100 \text{ mA}$ $I_{C} = 10 \text{ A}$ $I_{C} = 10 \text{ A}$ $I_{C} = 10 \text{ A}$	$T_c = 150$ °C $I_B = 40 \text{ mA}$ $I_B = 80 \text{ mA}$ $V_{CE} = 3 \text{ V}$	100		1 5 3 5	mA mA mA
Current (I _B = 0) Emitter Cut-off Current I _C = 0) Collector-Emitter Breakdown Voltage Collector-Emitter Saturation Voltage Base-Emitter Voltage OC Current Gain duration = 300 µs, duty cycle 1.	V _{EB} = 5 V I _C = 100 mA I _C = 10 A I _C = 16 A I _C = 10 A	I _B = 80 mA	100	-91	5	mA V
Ic = 0) Collector-Emitter Breakdown Voltage Collector-Emitter Saturation Voltage Base-Emitter Voltage OC Current Gain duration = 300 µs, duty cycle 1.	I _C = 100 mA I _C = 10 A I _C = 16 A I _C = 10 A	I _B = 80 mA	100	-91	cil	3)
Breakdown Voltage Collector-Emitter Saturation Voltage Base-Emitter Voltage OC Current Gain duration = 300 µs, duty cycle 1.	I _C = 10 A I _C = 16 A I _C = 10 A	I _B = 80 mA	100	-91	2.5	
Saturation Voltage Base-Emitter Voltage OC Current Gain duration = 300 µs, duty cycle 1.	I _C = 16 A	I _B = 80 mA		-9/	2.5	\/
DC Current Gain duration = 300 µs, duty cycle 1.		V _{CE} = 3 V			4	V
duration = 300 μs, duty cycle 1.	I _C = 10 A		01		3 (V
		$V_{CE} = 3 V$	1000		115	,
Produ	1(6)					
te Produ						
	te Produ	te Product(s)	te Product(s) obsolets e product(s)	Itage and current values are negative.	te Product(s) Obsolete Product(s) obsolete	te Product(s) Obsolete Product(s) obsolete

4 2/4

TO-3 MECHANICAL DATA

DIM.	mm		inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	11.00		13.10	0.433		0.516
В	0.97		1.15	0.038		0.045
С	1.50		1.65	0.059		0.065
D	8.32		8.92	0.327		0.351
Е	19.00		20.00	0.748	41)	0.787
G	10.70		11.10	0.421	2100	0.437
N	16.50		17.20	0.649		0.677
Р	25.00		26.00	0.584	-40	1.023
R	4.00		4.09	0.157	2/00	0.161
U	38.50		(19.30	1.515		1.547
V	30.00	16	30.30	1.187		1.193



3/4

homation furricus of sirianted is the state of sirianted is sirianted in sirianted is sirianted in sirianted is sirianted in sirianted is sirianted in sirianted in sirianted is sirianted in sirianted in sirianted in sirianted in sirianted in sirianted of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products

are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics.

All other names are the property of their respective owners.

© 2003 STMicroelectronics - All Rights reserved STMicroelectronics GROUP OF COMPANIES

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com

47/

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

STMicroelectronics:

MJ4032 MJ4035